

| INFORMATION DISCLOSURE CITATION IN AN APPLICATION  (PTO-1449) | | | | ATTY. DOCKET NO. 63979-028 | SERIAL NO. 10/616,917 |
|---|----------|---|--|---|---|
| | | | | APPLICANT Takashi NISHIKAWA, et al. | |
| | | | | FILING DATE July 11, 2003 | GROUP 2811 |
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| EXAMINER'S INITIALS | CITE NO. | Document Number Number-Kind Code ₂ (if known) | Publication Date MM-DD-YYYY | Name of Patentee or Applicant of Cited Document | Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear |
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| KR | US | 6,407,435 B1 | 06/18/2002 | Ma et al. | |
| | US | | | | |
| FOREIGN PATENT DOCUMENTS | | | | | |
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| | | | | | Yes No |
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| OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.) | | | | | |
| EXAMINER'S INITIALS | CITE NO. | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate),of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published. | | | |
| KR | | Mitsue Takahashi et al., "ANALYSIS AND IMPROVEMENT OF RETENTION TIME OF MEMORIZED STATE OF METAL-FERROELECTRIC-INSULATOR-SEMICONDUCTOR STRUCTURE FOR FERROELECTRIC GATE FET MEMORY". The Japan Society of Applied Physics, January 5, 2001, pp. 2923-2927 | | | |
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| EXAMINER <i>Kushal Rose</i> | | DATE CONSIDERED <i>1/19/05</i> | | | |

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.

| INFORMATION DISCLOSURE CITATION IN AN PTO APPLICATION | | | | ATTY. DOCKET NO. 63979-028 | SERIAL NO. 10/616,917 |
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| OTHER ART (including Author, title, Date, Pertinent Pages, Etc.) | | | | | |
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| | | Mitsue Takahashi et al., "ANALYSIS AND IMPROVEMENT OF RETENTION TIME OF MEMORIZED STATE OF METAL-FERROELECTRIC-INSULATOR-SEMICONDUCTOR STRUCTURE FOR FERROELECTRIC GATE FET MEMORY", The Japan Society of Applied Physics, January 5, 2001, pp. 2923-2927 | | | |
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